

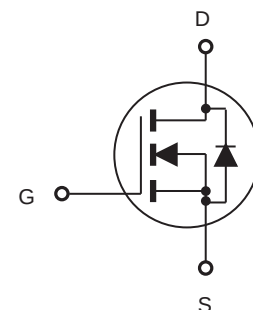
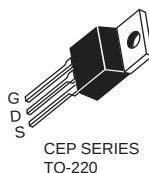
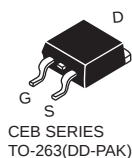


CEP6060R/CEB6060R

N-Channel Enhancement Mode Field Effect Transistor

FEATURES

- 60V, 60A, $R_{DS(ON)} = 25m\Omega$ @ $V_{GS} = 10V$.
- Super high dense cell design for extremely low $R_{DS(ON)}$.
- High power and current handling capability.
- Lead free product is acquired.
- TO-220 & TO-263 package.



ABSOLUTE MAXIMUM RATINGS $T_C = 25^{\circ}C$ unless otherwise noted

Parameter	Symbol	Limit	Units
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	60	A
Drain Current-Pulsed ^a	I_{DM}	144	A
Maximum Power Dissipation @ $T_C = 25^{\circ}C$ - Derate above $25^{\circ}C$	P_D	100	W
		0.7	W/ $^{\circ}C$
Single Pulsed Avalanche Energy ^d	E_{AS}	168	mJ
Single Pulsed Avalanche Current ^d	I_{AS}	58	A
Operating and Store Temperature Range	T_J, T_{stg}	-65 to 175	$^{\circ}C$

Thermal Characteristics

Parameter	Symbol	Limit	Units
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	2	$^{\circ}C/W$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	62.5	$^{\circ}C/W$

[查询"CEP6060R_06"供应商](#)



CEP6060R/CEB6060R

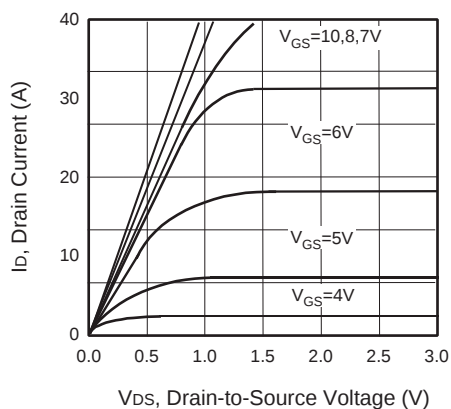


Figure 1. Output Characteristics

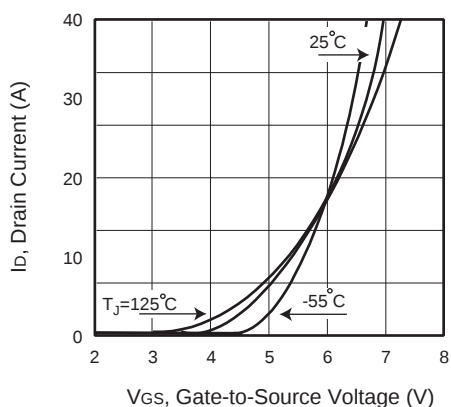


Figure 2. Transfer Characteristics

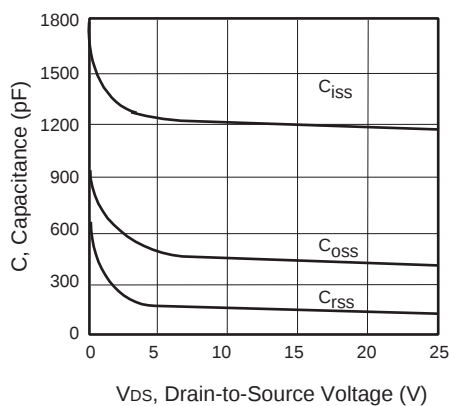


Figure 3. Capacitance

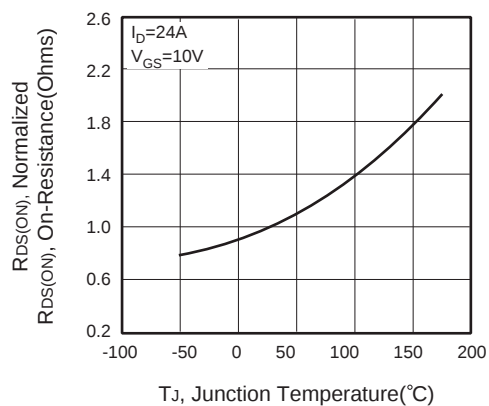


Figure 4. On-Resistance Variation with Temperature

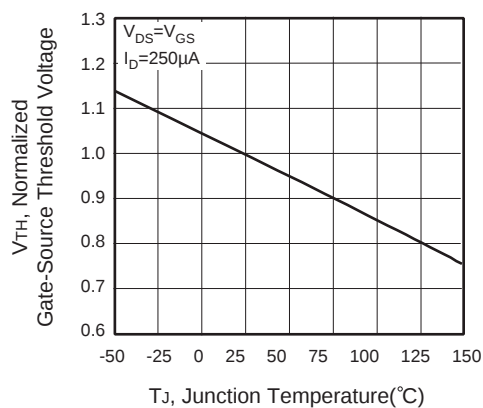


Figure 5. Gate Threshold Variation with Temperature

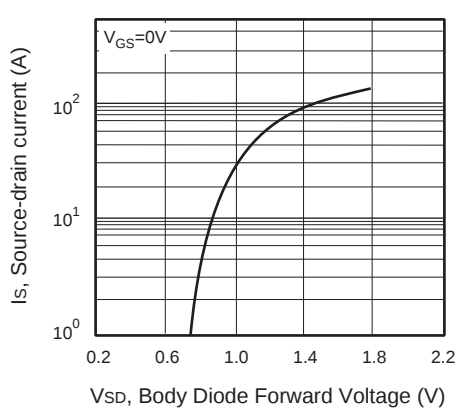


Figure 6. Body Diode Forward Voltage Variation with Source Current

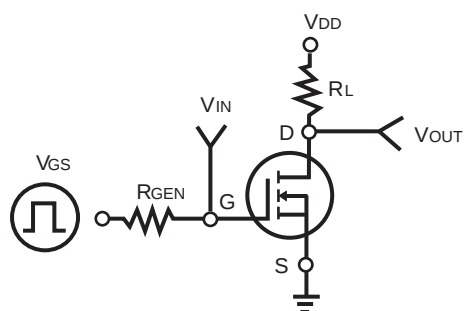
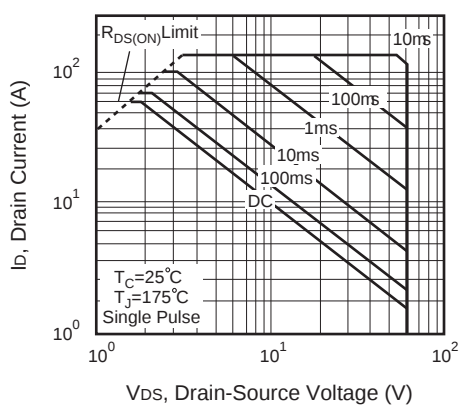
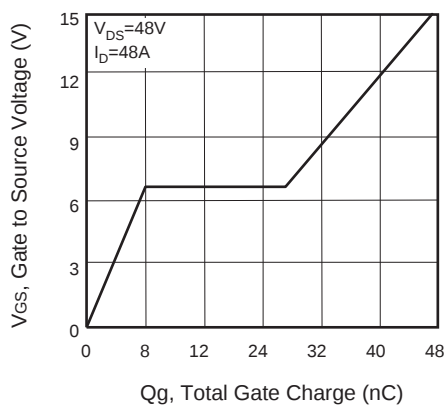


Figure 9. Switching Test Circuit

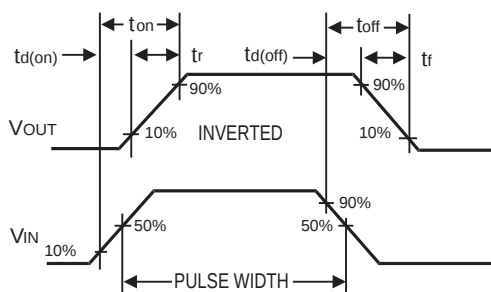


Figure 10. Switching Waveforms

